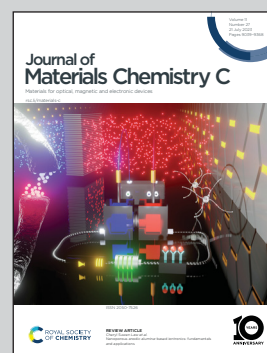


Showcasing research from Professor Tae Joo Park's laboratory, Department of Materials Science and Chemical Engineering, Hanyang University, Ansan, Republic of Korea.

High-quality SiN_x thin-film growth at 300 °C using atomic layer deposition with hollow-cathode plasma

High-quality SiN_x film was grown at low temperature using ALD with a novel remote plasma source (hollow cathode plasma), exhibiting low oxygen impurity concentration, low wet etch rate and high oxidation resistance.

As featured in:



See Woo-Hee Kim,
Tae Joo Park *et al.*,
J. Mater. Chem. C, 2023, **11**, 9107.